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MJ802 Silicon NPN Transistor High Power Audio Amplifier TO-3 Type Package

Description:

The MJ802 is a silicon NPN transistor in a TO3 type case designed for use as an output device in audio amplifiers to 100 watts music power per channel.

Features:

- High DC Current Gain: $h_{FE} = 25 - 100 @ I_C = 7.5A$
- Excellent Safe Operating Area
- Complement to the PNP MJ4502

Absolute Maximum Ratings:

Collector-Emitter Voltage, V_{CER}	100V
Collector-Base Voltage, V_{CB}	100V
Collector-Emitter Voltage, V_{CEO}	90V
Emitter-Base Voltage, V_{EB}	4V
Collector Current, I_C	30A
Base Current, I_B	7.5A
Total Device Dissipation ($T_C = +25^\circ C$), P_D	200W
Derate Above $25^\circ C$	1.14W/ $^\circ C$
Operating Junction Temperature Range, T_J	-65° to $+200^\circ C$
Storage Temperature Range, T_{stg}	-65° to $+200^\circ C$
Thermal Resistance, Junction-to-Case, R_{thJC}	0.875 $^\circ C/W$

Electrical Characteristics: ($T_C = +25^\circ C$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF Characteristics						
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	$I_C = 200mA, R_{BE} = 100\Omega$, Note 1	100	-	-	V
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 200mA$, Note 1	90	-	-	V
Collector-Base Cutoff Current	I_{CBO}	$V_{CB} = 100V, I_E = 0$	-	-	1.0	mA
		$V_{CB} = 100V, I_E = 0, T_C = +150^\circ C$	-	-	5.0	mA
Emitter-Base Cutoff Current	I_{EBO}	$V_{BE} = 4V, I_C = 0$	-	-	1.0	mA

Note 1. Pulse Test: Pulse Width $\leq 300\mu s$. Duty Cycle $\leq 2\%$.

Electrical Characteristics (Cont'd): ($T_C = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
ON Characteristics (Note 1)						
DC Current Gain	h_{FE}	$I_C = 7.5\text{A}, V_{CE} = 2\text{V}$	25	-	100	
Base-Emitter ON Voltage	$V_{BE(on)}$	$I_C = 7.5\text{A}, V_{CE} = 2\text{V}$	-	-	1.3	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 7.5\text{A}, I_B = 750\text{mA}$	-	-	0.8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 7.5\text{A}, I_B = 750\text{mA}$	-	-	1.3	V
Dynamic Characteristics						
Current Gain-Bandwidth Product	f_T	$I_C = 1\text{A}, V_{CE} = 10\text{V}, f = 1\text{MHz}$	2.0	-	-	MHz

Note 1. Pulse Test: Pulse Width $\leq 300\mu\text{s}$. Duty Cycle $\leq 2\%$.

